Structure of Er^{3+} -doped SiO₂-HfO₂ Glass and Glass-Ceramic Planar Waveguides using EXAFS and XRD

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 ${\rm Er}^{3+}$ -doped SiO₂ glasses represent the basic material used in the fabrication of photonics devices such as optical amplifiers. Having binary or ternary glassy hosts can lead to systems with better spectroscopic properties, compared to the basic SiO₂ glass. Introducing additional oxides is an attempt to enhance the limited solubility of the rare-earth ion. Another motivation is trying to alter the crystal field around these ions. Recently, this procedure has been extended to growing nanocrystalline phases of the co-dopant oxide, obtaining new materials where rare-earth ions are present in small nanocrystals dispersed in the host glass. Many co-dopant oxides such as Na₂O, TiO₂, and Al₂O₃ have been reported in literature, leading in most cases to improvement in the properties. Here we present results of introducing HfO₂ into the Er³⁺-doped SiO₂ glassy system. Both the glassy and glass-ceramic regimes were covered in this study.

Planar waveguides with the nominal compositions 1 mol % Er^{3+} -doped (1-x)SiO₂-xHfO₂ (x = 0.0, 0.9, 1.8, 5, 8, 10, 20, 30, 40, and 50 mol %) were prepared by the sol-gel route and dip-coated on amorphous SiO₂ substrates. All the samples were thermally annealed at 900°C for duration depending on HfO₂ content, obtaining fully densified amorphous waveguides. Nanocrystals of HfO₂ were successively grown by appropriate further thermal annealing. The structure of the glass and glass-ceramic waveguides was characterized by XRD and both Er and Hf L₃-edges EXAFS measurements carried on ESRF Beamlines.

In the glassy regime, our EXAFS results at Er L_3 -edge show the strong tendency of Er^{3+} ions to be present in HfO₂-rich regions for HfO₂ concentration $\geq 5 \mod \%$, without altering its local structure between 10 and 50 mol % HfO₂. These results were confirmed by both Photoluminescence (PL) and Raman results. At lower concentrations of HfO₂, the local structure around Er^{3+} is modified with respect to the pure SiO₂ host. In the glass-ceramic regime, even with 5 mol % HfO₂, it was possible to grow HfO₂ nanocrystals. Both Hf L_3 -edge EXAFS and XRD results evidence the substitution of Hf by Er ions in the nanocrystals. Er L_3 -edge EXAFS results clearly show an ordered environment around the rare-earth ion. This environment is sensitive to the size of HfO₂ nanocrystals, which in turn is tunable by controlling the heat treatment. These findings were found coherent with the measured PL spectra. Very similar results were obtained on waveguides fabricated by the RF-sputtering technique.

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